

Erratum: “Magnitude and sign control of lithography-induced uniaxial anisotropy in ultrathin (Ga,Mn)As wires” [Appl. Phys. Lett. 98, 083101 (2011)]

J. Shiogai,^{1,2,a)} D. Schuh,¹ W. Wegscheider,^{1,3} M. Kohda,^{2,4} J. Nitta,² and D. Weiss¹

¹*Institute of Experimental and Applied Physics, University of Regensburg, 93053 Regensburg, Germany*

²*Department of Materials Science, Tohoku University, 980-8579 Sendai, Japan*

³*Department of Physics, ETH Zürich, 8093 Zürich, Switzerland*

⁴*PRESTO, Japan Science and Technology Agency, 332-0012 Kawaguchi, Japan*

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In the originally published version of this letter the sentence on page 2 starting with “In the whole temperature range,...” is incomplete. Complete it should read as follows: “In the whole temperature range, the uniaxial AMR coefficient [the first term in Eq. (2)] for the 1- μm -wide wires is by a factor of 1.5 to 2 times larger than that for the 20- μm -wide wire [the first term in Eq. (1)].”

^{a)}Electronic mail: bltd5304@stu.material.tohoku.ac.jp.